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溅射时间对脉冲激光沉积制备 $\beta$ -FeSi<sub>2</sub>薄膜的影响

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摘要:

本文基于脉冲激光沉积 (PLD)方法及热退火处理方式, 利用输出波长为1064 nm的Nd:YAG脉冲激光器在P型Si (100) 衬底上生长了均匀的单相  $\beta$ -FeSi<sub>2</sub> 薄膜。采用X 射线衍射(XRD)、扫描电镜(SEM)、原子力显微镜 (AFM)分析技术, 研究了 $\beta$ -FeSi<sub>2</sub> 薄膜的结构、组分、结晶质量和表面形貌。结果发现, 在其他相同沉积条件下, 随着溅射时间的增加, 薄膜晶化程度、颗粒大小和形状、表面粗糙度都发生规律性变化, 通过分析比较得出, 在本实验条件下溅射时间为40 min制备的  $\beta$ -FeSi<sub>2</sub> 薄膜结晶质量较好。

关键词: 脉冲激光沉积 ( PLD ) &beta; -FeSi<sub>2</sub> 薄膜 溅射时间

Effects of sputtering time on the structure and morphology of  $\beta$ -FeSi<sub>2</sub> film made with pulsed laser deposition

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Abstract:

We made uniform single phase  $\beta$ -FeSi<sub>2</sub> films on Si (100) substrate with a Nd:YAG pulsed laser of 1064 nm (output wavelength), pulsed laser deposition (PLD) and thermal annealing process. We further investigated the structure and surface morphology with atomic force microscope (AFM), scanning electron microscope (SEM) and X-ray diffraction (XRD) method. Experimental results show the crystallization degree, size and shape of the grains and surface roughness are all regularly changed with the increase of sputtering time. We discovered that 40 minutes is the optimal sputtering time under the present experimental conditions after comparing the different sputtering time.

Keywords: PLD  $\beta$ -FeSi<sub>2</sub> films sputtering time

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- ▶ &beta;
- ▶ -FeSi<sub>2</sub> 薄膜
- ▶ 溅射时间

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